July 21, 1964

Dr. John Dismukes
Radio Corporation of America
RCA Laboratories
David Sarnoff Research Center
Princeton, New Jersey

Dear Dr. Dismukes:

Thank you very much for your letter of July 17 and for the samples of germanium and silicon powders and also the samples of phosphorus doped germanium - silicon material. We very much appreciate your generosity in making these materials available to us. We will certainly inform you of results as our research with these systems progresses.

Very truly yours,

H. Tracy Hall
Director of Research
Room 224 ELB

HTH/lw

RADIO CORPORATION OF AMERICA
RCA LABORATORIES
David Sarnoff Research Center
PRINCETON, N. J.

July 17, 1964

Prof. H. Tracy Hall
Director of Research
Room 224 E1B
Research Division
Brigham Young University
Provo, Utah

Dear Prof. Hall,

Enclosed are some samples of Ge and Si, both powders and slices from the batch we used for our studies.

Also included are samples of phosphorus doped 28at%Ge, slices 5,6,8,9 of ingot #100. The thermoelectric power of the material is about -530μV/°C at 300°K, carrier concentration about 1×10^{18} cm^{-3}.

I will cut more phosphorus doped samples from other compositions and send them later.

Sincerely,

John Dismukes

John Dismukes

JD:ez

Enclosure